

Notice of References Cited

Application No.

09/428,052

Applicant(s)

IRINO, KIYOSHI

Examiner

J. Diaz

Group Art Unit

2815

Page 1 of 1

U.S. PATENT DOCUMENTS

* DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
A 5,972,783	10/1999	Cerai et al.	438	513
B 5,880,508	3/1999	Wu	257	44
C 5,880,640	3/1999	Sun et al.	438	769
D 5,747,882	5/1998	Wang et al.	257	768
E 5,516,707	5/1996	Loh et al.	438	302
F 5,743,469	7/1998	Gardner et al.	438	199
G				
H				
I				
J				
K				
L				
M				

FOREIGN PATENT DOCUMENTS

* DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
N					
O					
P					
Q					
R					
S					
T					

NON-PATENT DOCUMENTS

* DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
U Marti et al., "Oxynitride Gate Dielectric Grown in Nitric Oxide (NO): Threat of Recombination on Dielectric Reliability of the Active Edge", IEEE Electron Device Letters, vol. 17 Issue 6, June 1996 pp. 279-281	
V Min et al., "Impact of process-induced damage on MOSFET reliability and suppression of damage by the use of NO-based oxynitride gate dielectrics", VLSI Technology, Systems and Applications, 1995. Proceedings of Technical papers. 1995 International Symposium pp. 273-276	
W Bhat et al., "Performance and hot-carrier reliability of N- and PMOSFETs with rapid thermally NO-nitrided SiO2 gate dielectrics", Electron Devices Meeting, 1994. Technical Digest, International 1994, pp. 329-332	
X Bhat et al., "Electrical properties and reliability of MOSFETs with rapid thermal NO-nitrided SiO2 gate dielectrics, Electron devices, IEEE Transactions on May 1995, vol. 42 Issue 5 Part 1, pp. 907-914	

* A copy of this reference is not being furnished with this Office action.
(See Manual of Patent Examining Procedure, Section 707.05(a).)